

Schottky Barrier Diodes for General Purpose Applications

Technical Data

1N5711
1N5712
5082-2300 Series
5082-2800 Series
5082-2900

Features

- **Low Turn-On Voltage**
As Low as 0.34 V at 1 mA
- **Pico Second Switching Speed**
- **High Breakdown Voltage**
Up to 70 V
- **Matched Characteristics Available**

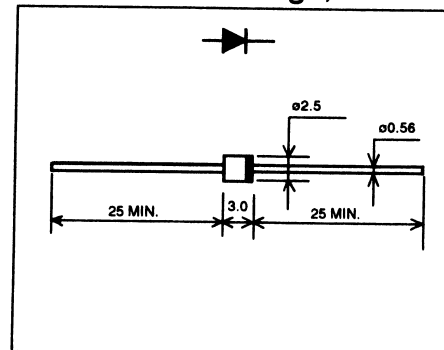
Description/Applications

The 1N5711, 1N5712, 5082-2800/10/11 are passivated Schottky barrier diodes which use a patented "guard ring" design to achieve a high breakdown voltage. Packaged in a low cost package, they are well suited for high level detecting, mixing, switching, gating, log or A-D converting, video detecting, frequency discriminating, sampling, and wave shaping.

The 5082-2835 is a passivated Schottky diode in a low cost package. It is optimized for low turn-on voltage. The 5082-2835 is particularly well suited for the UHF mixing needs of the CATV marketplace.

The 5082-2300 Series and 5082-2900 devices are unpassivated Schottky diode package. These diodes have extremely low 1/f noise and are ideal for low noise mixing, and high sensitivity detecting. They are particularly well suited for use in Doppler or narrow band video receivers.

■ Outline drawings, mm



Maximum Ratings

Junction Operating and Storage Temperature Range

5082-2303, -2900	-60°C to +100°C
1N5711, 1N5712, 5082-2800/10/11	-65°C to +200°C
5082-2835	-60°C to +150°C

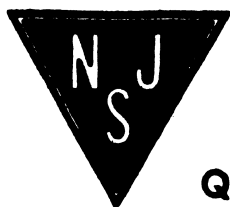
DC Power Dissipation

(Measured in an infinite heat sink at $T_{CASE} = 25^{\circ}\text{C}$)

Derate linearly to zero at maximum rated temperature

5082-2303, -2900	100 mW
1N5711, 1N5712, 5082-2800/10/11	250 mW
5082-2835	150 mW

Peak Inverse Voltage V_{BR}



Quality Semi-Conductors